

PRODUCT/PROCESS CHANGE NOTIFICATION

PCN APM/08/3425 Notification Date 02/18/2008

New location for PDIP 8-14-16L packages in Nantong Fujitsu (CHINA)

APM - APM

Table 1. Change Implementation Schedule

Forecasted implementation date for change	08-May-2008		
Forecasted availability date of samples for customer	11-Feb-2008		
Forecasted date for STMicroelectronics change Qualification Plan results availability	11-Feb-2008		
Estimated date of changed product first shipment	19-May-2008		

Table 2. Change Identification

Product Identification (Product Family/Commercial Product)	See attached list
Type of change	Package assembly location change
Reason for change	To improve service and increase our capacity
Description of the change	Following ST commitment towards a continuous improvement of service, it has been decided to increase PDIP 8-14-16 production capacity setting up a new Assembly & Testing location in Nantong Fujitsu (NFME) plant (CHINA). PDIP 8-14L packages are qualified for assembly process for Std Linear Division in NFME, while PDIP16L package is qualified for assembly and testing process for Std Digital Division. Currently, NFME is a ST qualified subcontractor for many other large volume packages. Either the electrical and mechanical characteristics and the level of quality and reliability of product manufactured in NFME are aligned to ST standard. Samples for devices used as Test Vehicles are available.
Product Line(s) and/or Part Number(s)	See attached
Description of the Qualification Plan	See attached
Change Product Identification	"GF" (Assy plant code) as first digits on the label traceability code
Manufacturing Location(s)	

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Table 3. List of Attachments	Tal	ble	3. L	ist	of	Attac	chm	ents
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Customer Part numbers list	
Qualification Plan results	

Customer Acknowledgement of Receipt	PCN APM/08/3425
Please sign and return to STMicroelectronics	Sales Office Notification Date 02/18/2008
□ Qualification Plan Denied	Name:
□ Qualification Plan Approved	Title:
	Company:
□ Change Denied	Date:
□ Change Approved	Signature:
Remark	
1	

47/.

DOCUMENT APPROVAL

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Gilot, Yves	Division Marketing Manager
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Russo, Biagio	Division Product Manager
Lisi, Giuseppe	Division Q.A. Manager
Paccard, Francoise	Division Q.A. Manager

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Reliability Report

On DIP16 - NFME subcontractor - FULL RIVER Frame

General Information

Product Line : P53B

: TRIPLE 2-CHANNEL
Product Description ANALOG MULTIPLEXER/

DEMULTIPLEXER

Commercial Product : HCF4053BEY

Product Group : Advanced Analog Logic

Product Division : IMS - APM GROUP

Package Description : DIP 16L Silicon Process Technology : NHFSFII Locations

Wafer fabrication location : ANGMOKIO

Assembly plant location : NFME

NANTONG FUJISU

Final test plant location : NFME

NANTONG FUJISU

DOCUMENT HISTORY

Version	Date	Pages	Author	Comment
0.1	20-July-07	8	A. Basile G. Presti	Original document

Reliability is the attitude of element to satisfy required function in fixed conditions during established time.

Note: This report is a summary of the reliability trials performed in good faith by STMicroelectronics in order to evaluate the potential reliability risks during the product life using a set of defined test methods.

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Report ID: REL6043-262W07



1 RELIABILITY EVALUATION OVERVIEW

1.1 Objectives

Aim of this report is to present the results of the reliability evaluations performed on HCF4053B device in order to qualify DIP14/16 package assembled in NFME subcontractor.

This product is processed in NHSFII technology, diffused in ST ANGMOKIO plant and assembled in DIP16 package using FULL RIVER Lead Frame.

1.2 Conclusion

The final reliability results are positive for all stressed lots.

2 DEVICE CHARACTERISTICS

2.1 Device description

HCF4053B - TRIPLE 2- CHANNEL ANALOG MULTIPLEXER /DEMULTIPLEXER (Datasheet rev. October 2002). The HCF4053B is a monolithic integrated circuit fabricated in Metal Oxide Semiconductor.tecnology available in DIP Package. It is a digitally controlled analog switch having low ON impedance and very low OFF leakage current.

2.2 Traceability

2.2.1 Wafer fabrication information

- Wafer fabrication manufacturing location: ANGMOKIO
- Technology: NHFSII
- Die size: 1.349 X 1.572
- Passivation type: PVAPOX

2.2.2 Assembly information

- Assembly site: NFME (NANTONG FUJITSU)
- Package description: DIP16
- > Frame: FULLRIVER
- Wire: Au

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3 RELIABILITY TESTS RESULTS

3.1 Reliability test plan and results summary

Include here the tests plan and the results summary.

Die oriented test

	Test short desc	ription				900
Test	Method	C	onditions	Sample Size	Duration	Results Fail/ Sample Size
нтв	High Temperatur	e Bias		4	A -	
111111111111111111111111111111111111111		TA=125℃ Vbias=	=18V	77x1 Lot	1000h	0/77
	High Temperatur	e Storage				
HTS				77x3 Lots	1000h	0/231

Package oriented test

	Test short desc	ription				
Test	Method	Conditions	Sample Size	Duration	Results Fail/ Sample Size	
T.H.B.	Temperature Humidity Bias					
1.H.D.		TA=85℃ – RH=85%, Vbias=15V	77x3 Lots	1000h	0/231	
T.C.	Thermal Cycle	1				
1.0.		TA=-65℃ TO 150℃ (1 HOUR/CYCLE)	77x3 Lots	500cy	0/231	
P.P.	Pressure Pot					
F.F.		TA=121℃ – PA=2ATM	77x3 Lots	168h	0/231	
				•		

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LATCH - UP

5.1 Input and Output Injection Latch-up.

TEST CONDITIONS	
TEST ENVIRONMENT	Automated DC Bench
SAMPLE SIZE	4 Devices
TEMPERATURE	+25°C
SUPPLY VOLTAGE	Vcc=5.5V
TEST METHOD	UDCS 0018695

TEST DESCRIPTION

Negative Current Trigger (NIT):

Input and Output pins injected with current sweep from 0mA to -500mA, -50mA steps Tested output conditions:

- 1) Active; Output conditioned LOW
- 2) 3-state mode

Results:

No Latch - up was observed

ESD tests

TEST CONDITIONS	
Date 23/01/2008	
Type of test	
IMCM System	Keytek
Zap Circuit	HBM11-C
Testing Program	manual bench
Failure Criteria	Functional and electrical Parameters
Test Method	JESD22-A115
Devices	HCF4053
Package	DIP16

Made by: Angelo Castro

	Zap Voltage (kV)	n. of Zap	Zap vs Vcc	Zap vs GND	Zap vs I/O pin	Zap +	Zap +	Zap -	n.	of Sample	Results
b								Zapped	Failed		
	2	1	у	у	у	у	у	3	0	oĸ	

ESD test is SATISFACTORY.

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3.2 Die oriented tests

These tests are performed in order to demonstrate the quality and reliability of devices subjected to an elevated temperature and reverse biased.

The purpose of this test is to detect surface defects such as poor passivation, presence of contaminants, metal corrosion, etc

3.3 Package oriented tests

These tests are performed in order to check device life in various environmental conditions in an accelerated way. Detectable failure mechanisms are metal corrosion and molding defect, cracking of die, breaking of wire bonding, mechanical damage to the device case.

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4 APPLICABLE AND REFERENCE DOCUMENTS

Document reference Short description

AEC-Q100 : Stress test qualification for integrated circuits SOP 2610 : General product qualification procedure

Internal : Reliability Tests and criteria for qualifications (CORPORATE Q&R RULES)

ST specification

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5 GLOSSARY

ESD : Electro Static Discharge

LU : Latch Up

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6 ANNEXES



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Reliability Report

On DIP16 - NFME subcontractor -MHT Frame

General Information

Product Line : P53B

: TRIPLE 2-CHANNEL

Product Description ANALOG

MULTIPLEXER/DEMULTIPL

EXER

Commercial Product : HCF4053BEY

Product Group : Advanced Analog Logic

Product Division : IMS - APM GROUP

Package Description : DIP 16L Silicon Process Technology : NHFSFII Locations

Wafer fabrication location : ANGMOKIO

Assembly plant location : NFME

NANTONG FUJISU

Final test plant location

: NFME

NANTONG FUJISU

DOCUMENT HISTORY

Version	Date	Pages	Author	Comment				
0.1	20-July-07	8	A. Basile G. Presti	Original document				
		4						

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- ➤ Technology: NHFSII
- Die size: 1.349 X 1.572
- Passivation type: PVAPOX

2.2.2 Assembly information

- Assembly site: NFME (NANTONG FUJITSU)
- Package description: DIP16
- Frame: MHT
- Wire: Au

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3 RELIABILITY TESTS RESULTS

3.1 Reliability test plan and results summary

Include here the tests plan and the results summary.

Die oriented test

	Test short desc	Test short description									
Test	Method		Conditions		Sample Size	Duration	Results Fail/ Sample Size				
нтв	High Temperature Bias										
ПБ		TA=125℃	Vbias=18V		77x1 Lot	1000h	0/77				
	High Temperatur	re Storage									
HTS					77x3 Lots	1000h	0/231				

Package oriented test

	Test short description									
Test	Method	Conditions	Sample Size	Duration	Results Fail/ Sample Size					
T.H.B.	Temperature Humidity Bias									
1.11.0.		TA=85℃ – RH=85%, Vbias=15V	77x3 Lots	1000h	0/231					
T.C.	Thermal Cycle									
1.0.		TA=-65℃ TO 150℃ (1 HOUR/CYCLE)	77x3 Lots	500cy	0/231					
P.P.	Pressure Pot									
Г.Г.		TA=121℃ – PA=2ATM	77x3 Lots	168h	0/231					

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LATCH - UP

5.1 Input and Output Injection Latch-up.

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TEMPERATURE	+25°C
SUPPLY VOLTAGE	Vcc=5.5V
TEST METHOD	UDCS 0018695

TEST DESCRIPTION

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ESD tests

TEST CONDITIONS	
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Type of test	
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Testing Program	manual bench
Failure Criteria	Functional and electrical Parameters
Test Method	JESD22-A115
Devices	HCF4053
Package	DIP16

Made by: Angelo Castro

	Zap Voltage (kV)	n. of Zap	Zap vs Vcc	Zap vs GND	Zap vs I/O pin	Zap +	Zap +	Zap -	n.	of Sample	Results
b								Zapped	Failed		
	2	1	у	у	у	у	у	3	0	oĸ	

ESD test is SATISFACTORY.

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3.2 Die oriented tests

These tests are performed in order to demonstrate the quality and reliability of devices subjected to an elevated temperature and reverse biased.

The purpose of this test is to detect surface defects such as poor passivation, presence of contaminants, metal corrosion, etc

3.3 Package oriented tests

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ST specification

. .

5 GLOSSARY

ESD : Electro Static Discharge

LU : Latch Up

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6 ANNEXES



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Reliability Report

Assembly qualification

General Information

Product Line : 0393

Product Description : Dual comparator

Commercial Product : LM393N Product Group : APM

Product Division : Standard IC's
Package Description : Minidip 8
Silicon Process Technology : Bipolar

Locations

Wafer fabrication location : Ang Mo Kio

Assembly plant location : Nantong Fujitsu China Final test plant location : ST Shenzhen China

General Information

Product Line : 0124

Product Description : Dual Operational amplifier

Commercial Product : LM324N Product Group : APM

Product Division : Standard IC's
Package Description : DIP14
Silicon Process Technology : Bipolar

Locations

Wafer fabrication location : Ang Mo Kio

Assembly plant location : Nantong Fujitsu China Final test plant location : ST Shenzhen China

DOCUMENT HISTORY

Version	Date	Pages	Author	Comment
0.1	24-Jan-07	5	JM Bugnard	Original document

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	Error! Bookmark not defined.	
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1 RELIABILITY EVALUATION OVERVIEW

1.1 Objectives

This Qualification Report summarizes the reliability trials and results performed to qualify the DIP package, Nantong Fujitsu China assembly line.

This document is the official report of the qualification of the DIP package Nantong Fujitsu China assembly plant for standard linear Ic's.

The test conditions and results are presented in chapter 3.

1.2 Conclusion

Based on reliability results and construction analysis results, DIP8 and 14 leads assembled in Nantong Fujitsu China are qualified for standard linear IC's

2 DEVICE CHARACTERISTICS

2.1 Device description

	TV1	TV2	
Line	0393	0124	
Sales Type	LM393N	LM324N	
Diffusion site	Ang Mo Kio	Singapore	
FE process	Bipolar	Bipolar	
Package	DIP8	DIP14	
Die size (µm)	950 X 870 µm	1430 X 1360 µm	
Die thickness (µm)	280µm	280µm	
Metallization	AlSiCu	AlSiCu	
Passivation	Nitride	Nitride	
Back side	Raw silicon	Raw silicon	

2.2 TRACEABILITY

2.2.1 Assembly information

	New
Assembly location	Nantong-Fujitsu China
Die attach	Yil HUA 9005SP-2
Wire	Gold 1 Mils
Leadframe	Copper 80x80 mils for DIP14
	100x100mils for DIP8
Molding compound	HYSOL HUA WEI KLA4000-1T
Lead finishing	Sn plating

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3 RELIABILITY TESTS RESULTS

Include here a general description of the reliability evaluation strategy. If the test plan is not in line with the one planned initially, include necessary explanation.

3.1 Reliability test plan and results summary

Die oriented test

	Test short description						
Test	Method	Conditions	Sample Size	Duration	Results Fail/ Sample Size		
НТВ	LM393N						
ПІБ		Tamb= 150℃ , Vcc=+/-15V	78	1000h	0/78		
HTB							
		Tamb= 150℃ , Vcc=+/-15V	78	1000h	0/78		

Package oriented test

Test	Test short description						
	Method	Conditions	Sample Size	Duration	Results Fail/ Sample Size		
THB	LM393N						
	JEDEC JESD22 A101	Tamb.: 85℃, Rel. Humidity: 85%, Vcc: +/- 15V	78	1000h	0/78		
THB	LM324N						
	JEDEC JESD22 A101	Tamb.: 85℃, Rel. Humidity: 85%, Vcc: +/- 15V	78	1000h	0/78		
PPT	LM393N						
	JEDEC JESD22 A102	T°amb.:121°c, Presure: 2 atm	54	240h	0/54		
TMC	LM393N						
	JEDEC JESD22 A104C	Tamb.:-65/+150c (2 cycles per hour) air to air	78	1000cy	0/78		
TMC	LM324N						
	JEDEC JESD22 A104C	Tamb.:-65/+150c (2 cycles per hour) air to air	78	1000cy	0/78		

Conclusion: Based on these results and on construction analysis performed on these packages, DIP package is qualified for standard linear Ic's in Nantong Fujitsu (China).

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4 APPLICABLE AND REFERENCE DOCUMENTS

Document reference Short description

AEC-Q100 : Stress test qualification for integrated circuits SOP 2610 : General product qualification procedure

5 GLOSSARY

PC : Preconditioning

ESD : Electro Static Discharge HTB : High Temperature Bias

THB : Temperature and Humidity Bias

PPT : Pressure Pot TMC : Thermal Cycling

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